	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L2	3021	"semiconductor energy laboratory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/05 10:00
2	BRS	L3	169868 4	active adj matrix display	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/05 10:01
3	BRS	L4	19675	"semiconductor film"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/05 10:01
4	BRS	L5	1497	(active adj matrix display) and "semiconductor film" and (crystallized or crystallization or crystalizing) and "semiconductor energy laboratory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/05 10:01
5	BRS	L6	0	(active adj matrix display) same "semiconductor film" same (crystallized or crystallization or crystalizing) same "semiconductor energy laboratory"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/05 10:01

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	254	(active adj matrix display) same "semiconductor film" same (crystallized or crystallization or crystalizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
7	BRS	L8	4883	active adj matrix adj display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
8	BRS	L9	228418	crystallized or crystallization or crystallizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
9	BRS	L1	9	((active adj matrix adj display) same "semiconductor film" same (crystallized or crystallization or crystalizing)) and "semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
10	BRS	L10	264	(active adj matrix adj display) and "semiconductor film" and (crystallized or crystallization or crystallizing) and "semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	48527	"selected portion"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:21
12	BRS	L12	54281	"active layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:21
13	BRS	L13	459589	wiring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22
14	BRS	L14	214	10 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22
15	BRS	L15	183	14 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	8	15 and 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22

	Type	Hits	Search Text
1	BRS	3021	"semiconductor energy laboratory"
2	BRS	1698684	active adj matrix display
3	BRS	19675	"semiconductor film"
4	BRS	1497	(active adj matrix display) and "semiconductor film" and (crystallized or crystallization or crystalizing) and "semiconductor energy laboratory"
5	BRS	0	(active adj matrix display) same "semiconductor film" same (crystallized or crystallization or crystalizing) same "semiconductor energy laboratory"
6	BRS	254	(active adj matrix display) same "semiconductor film" same (crystallized or crystallization or crystalizing)
7	BRS	4883	active adj matrix adj display
8	BRS	228418	crystallized or crystallization or crystallizing
9	BRS	9	((active adj matrix adj display) same "semiconductor film" same (crystallized or crystallization or crystalizing)) and "semiconductor energy laboratory"
10	BRS	264	(active adj matrix adj display) and "semiconductor film" and (crystallized or crystallization or crystallizing) and "semiconductor energy laboratory"
11	BRS	48527	"selected portion"
12	BRS	54281	"active layer"

	DBs	Time Stamp
1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:43
2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:01
10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:24
11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:21
12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:21

	Type	Hits	Search Text
13	BRS	459589	wiring
14	BRS	214	((active adj matrix adj display) and "semiconductor film" and (crystallized or crystallization or crystallizing) and "semiconductor energy laboratory") and wiring
15	BRS	183	(((active adj matrix adj display) and "semiconductor film" and (crystallized or crystallization or crystallizing) and "semiconductor energy laboratory") and wiring) and "active layer"
16	BRS	8	((((active adj matrix adj display) and "semiconductor film" and (crystallized or crystallization or crystallizing) and "semiconductor energy laboratory") and wiring) and "active layer") and "selected portion"
17	IS&R	2	("6307243").PN.
18	BRS	17	("5118924" | "5298366" | "5300263" | "5384231" | "5420634" | "5453876" | "5479049" | "5559336" | "5610390" | "5666175" | "5693967" | "5701008" | "5796154" | "5844289" | "6040591" | "6104021" | "6171883").PN.
19	IS&R	715	(438/30).CCLS.
20	IS&R	1013	(438/151).CCLS.
21	IS&R	654	(438/164).CCLS.
22	IS&R	834	(438/166).CCLS.
23	IS&R	479	(438/486).CCLS.

	DBs	Time Stamp
13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22
14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22
15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 10:22
16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 15:36
17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/05 15:36
18	USPAT	2004/11/05 15:37
19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:43
20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:44
21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:44
22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:44
23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:44

	Type	Hits	Search Text
24	IS&R	460	(438/487).CCLS.

	DBs	Time Stamp
24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 15:44